



3DD5

NPN Silicon Low Frequency High Power Transistor



Features:

1. Using triple-diffusion process.Excellent capacity in anti-burnout.Excellent second breakdown capacity.
2. Good temperature stability.Excellent thermal fatigue capability.
3. Implementation of standards: GJB33-85, QZJ840611A, QZJ840611
4. Use for Low-speed switch,low frequency power amplify,power adjustment.
5. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA:

(Ta = 25°C)

Parameter name	Symbols	Unit	Specifications									Test Condition
			A	B	C	D	E	F	G	H	I	
Collector-Emitter Voltage	V _{CEO}	V	50	100	150	200	250	300	400	500	600	
Emitter-Base Voltage	V _{EBO}	V	5									
Max. Collector Current	I _{CM}	A	A~F:2.0, G~I:1.5									
Max. Collector Dissipation	P _{CM}	W	25									(Tc:75°C)
Junction Temperature	T _{jm}	°C	175									
Storage Temperature	T _{stg}	°C	-55~+175									
Collector-Emitter Leakage Current	I _{CEO}	mA	Max.:0.5									A:V _{CE} =30V;B:V _{CE} =50V; C~I:V _{CE} =100V
Collector- Emitter Saturation Voltage Drop	V _{CE(sat)}	V	Max.:1.0									A~F: I _C =1.0A, I _B =0.1A
			Max.:1.5									G~I: I _C =0.75A, I _B =0.15A
DC Current Gain	h _{FE}		Max.:120						Min.:15			A~F: V _{CE} =5V, I _C =1.0A
			Max.:120						Min.: 7			G~I:V _{CE} =10V, I _C =0.75A
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	V	A	B	C	D	E	F	G	H	I	I _C =1mA
			50	100	150	200	250	300	400	500	600	
E-Base Breakdown Voltage	V _{(BR)EBO}	V	5									I _E =0.5mA

h_{FE} Colored:

Color	Brown	Red	Orange	Yellow	Green	Blue
h _{FE}	7~15	15~25	25~40	40~55	55~80	80~120

Outline and Dimensions: